Thyristor Semiconductor Device - Page 1 of 1



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Inclosure Materia	al:
Metal	
Overall Length:	
Between 0.240 in	ches and 0.260 inches
Terminal Length	:
1.500 inches	
Overall Diameter	r:
Between 0.335 in	ches and 0.370 inches
End Application:	:
2350-01-087-109	5 tank, combat, full tracked
Internal Configu	ration:
Junction contact	
Mounting Metho	d:
Terminal	
Terminal Circle I	Diameter:
0.200 inches	
Features Provide	ed:
Burn in	
Criticality Code	Justification:
Feat	
Semiconductor I	Material:
Silicon	
Voltage Rating I	n Volts Per Characteristic:
100.0 reverse vo	Itage, peak and 150.0 nonrepetitive peak reverse voltage, peak total value
Current Rating P	Per Characteristic:
0.22 amperes for	ward current, total rms megahertz and 15.00 amperes forward current, average preset
Maximum Opera	ting Tempurature Per Measurement Point:
125.0 degrees ce	Isius junction
Special Features	s:
Nuclear hardness	critical item; junction pattern arrangement: pnpn
Terminal Type A	nd Quantity:
3 uninsulated wire	e lead
Shelf Life:	
N/a	
Unit Of Measure	:
Demilitarization:	
No	
Fiig:	
A110a0	